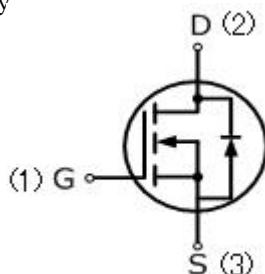


5N70GS

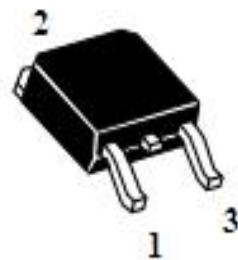
5 Amps, 700 Volts N-Channel Super Junction Power MOSFET

FEATURE

- 5A, 700V, $R_{DS(ON)MAX}=1.2\ \Omega$ @ $V_{GS}=10V/2.5A$
- Low gate charge
- Low C_{iss}
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability



TO-252



Absolute Maximum Ratings ($T_c=25^\circ C$, unless otherwise noted)

Parameter	Symbol	5N70GS	UNIT
Drain-Source Voltage	V_{DSS}	700	V
Gate-Source Voltage	V_{GSS}	± 30	
Continuous Drain Current	I_D	5	A
Pulsed Drain Current (Note 1)	I_{DM}	15	
Single Pulse Avalanche Energy (Note 2)	E_{AS}	30	mJ
Avalanche Current (Note 1)	I_{AR}	2.5	A
Repetitive Avalanche Energy (Note 1)	E_{AR}	0.4	mJ
Reverse Diode dV/dt (Note 3)	dV/dt	15	V/ns
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C
Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	T_L	260	°C

Thermal Characteristics

Parameter	Symbol	5N70GS	Units
Maximum Junction-to-Case	R_{thJC}	2.75	°C/W
Maximum Power Dissipation	$T_c=25^\circ C$	45	W

Electrical Characteristics ($T_c=25^\circ\text{C}$, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$\text{V}_{\text{GS}}=0\text{V}, \text{I}_D=250\mu\text{A}$	700	—	—	V
Breakdown Temperature Coefficient	$\Delta \text{BV}_{\text{DSS}} / \Delta T_J$	Reference to 25°C , $\text{I}_D=250\mu\text{A}$	—	0.6	—	$\text{V}/^\circ\text{C}$
Zero Gate Voltage Drain Current	I_{DS}	$\text{V}_{\text{DS}}=700\text{V}, \text{V}_{\text{GS}}=0\text{V}$	—	—	1	μA
Gate-Body Leakage Current, Forward	I_{GSSF}	$\text{V}_{\text{GS}}=30\text{V}, \text{V}_{\text{DS}}=0\text{V}$	—	—	1	μA
Gate-Body Leakage Current, Reverse	I_{GSSR}	$\text{V}_{\text{GS}}=-30\text{V}, \text{V}_{\text{DS}}=0\text{V}$	—	—	-1	μA
On Characteristics						
Gate-Source Threshold Voltage	$\text{V}_{\text{GS(th)}}$	$\text{V}_{\text{DS}}=\text{V}_{\text{GS}}, \text{I}_D=250\mu\text{A}$	2	—	4	V
Drain-Source On-State Resistance	$\text{R}_{\text{DS(on)}}$	$\text{V}_{\text{GS}}=10\text{V}, \text{I}_D=2.5\text{A}$	—	1.0	1.2	Ω
Dynamic Characteristics						
Input Capacitance	C_{iss}	$\text{V}_{\text{DS}}=50\text{V}, \text{V}_{\text{GS}}=0\text{V},$ $f=1.0\text{MHz}$	—	460	—	pF
Output Capacitance	C_{oss}		—	45	—	pF
Reverse Transfer Capacitance	C_{rss}		—	3.5	—	pF
Switching Characteristics						
Turn-On Delay Time	$t_{\text{d(on)}}$	$\text{V}_{\text{DD}}=380\text{V}, \text{I}_D=5\text{A},$ $\text{R}_G=18\Omega$ (Note 4,5)	—	6	—	ns
Turn-On Rise Time	t_r		—	3	—	ns
Turn-Off Delay Time	$t_{\text{d(off)}}$		—	50	—	ns
Turn-Off Fall Time	t_f		—	9	—	ns
Total Gate Charge	Q_g	$\text{V}_{\text{DS}}=480\text{V}, \text{I}_D=5\text{A},$ $\text{V}_{\text{GS}}=10\text{V}, (\text{Note 4,5})$	—	10	—	nC
Gate-Source Charge	Q_{gs}		—	1.6	—	nC
Gate-Drain Charge	Q_{gd}		—	4.0	—	nC
Drain-Source Body Diode Characteristics and Maximum Ratings						
Continuous Diode Forward Current	I_S	$\text{I}_S=5\text{A}, \text{V}_{\text{GS}}=0\text{V}$	—	—	5	A
Pulsed Diode Forward Current	I_{SM}		—	—	15	A
Diode Forward Voltage	V_{SD}	$\text{V}_{\text{GS}}=0\text{V}, \text{I}_S=5\text{A},$ $d\text{I}_F/dt=100\text{A/us}, (\text{Note 4})$	—	—	1.3	V
Reverse Recovery Time	t_{rr}		—	250	—	ns
Reverse Recovery Charge	Q_{rr}		—	2.2	—	μC

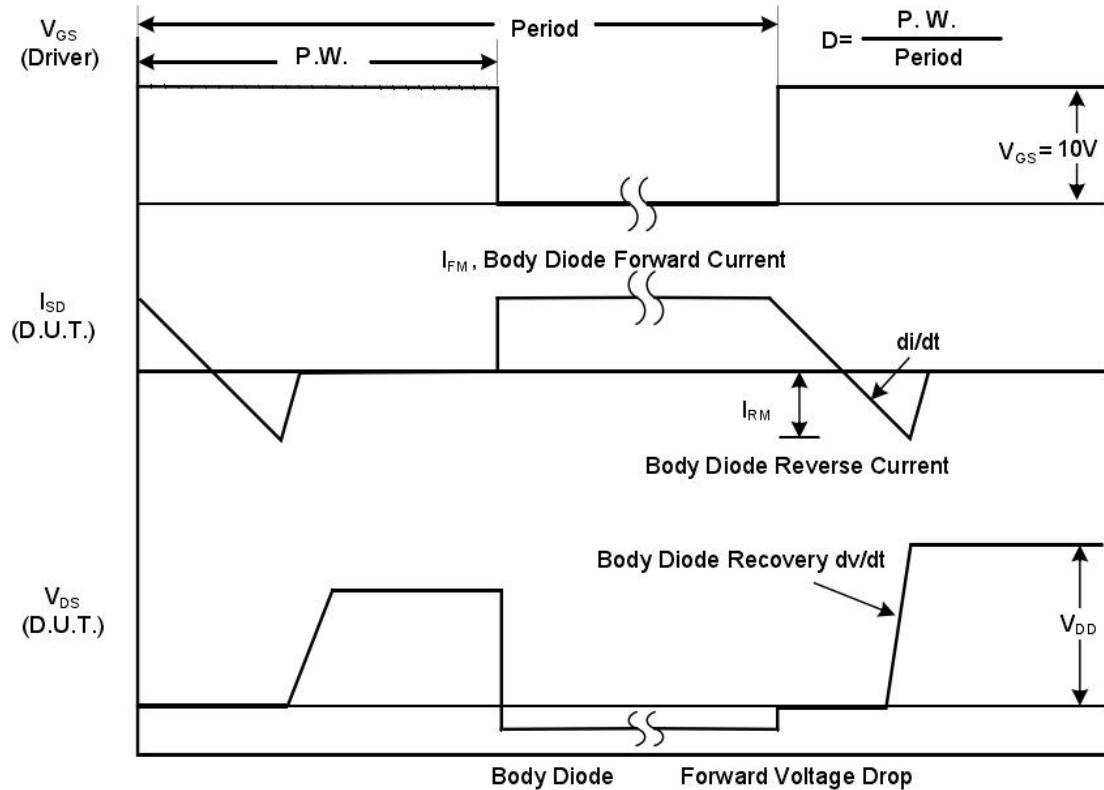
Notes

- Repetitive Rating; pulse width limited by maximum junction temperature.
- $\text{V}_{\text{DD}}=50\text{V}, L=10\text{mH}, R_g=25\Omega, I_{AS}=2.5\text{A}$, starting $T_J=25^\circ\text{C}$.
- $I_{SD} \leq I_D, dI/dt = 200\text{A/us}, V_{DD} \leq \text{BV}_{\text{DSS}}$, starting $T_J=25^\circ\text{C}$.
- Pulse width $\leq 300\text{us}$; duty cycle $\leq 2\%$.
- Repetitive rating; pulse width limited by maximum junction temperature.

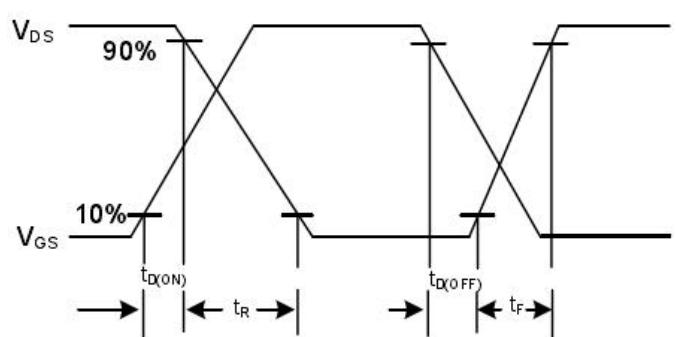
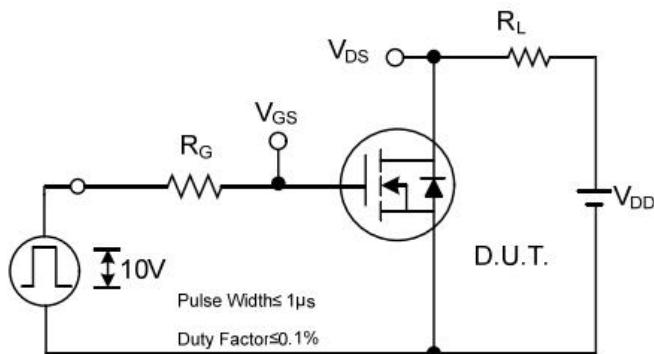
TEST CIRCUIT AND WAVEFORM



Peak Diode Recovery dv/dt Test Circuit

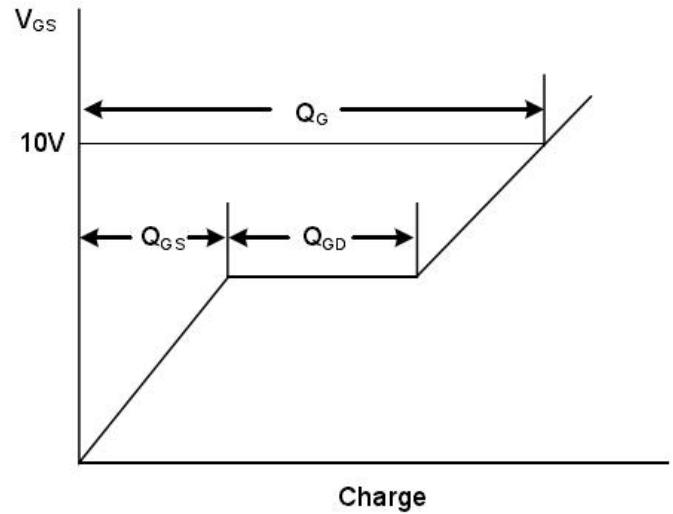
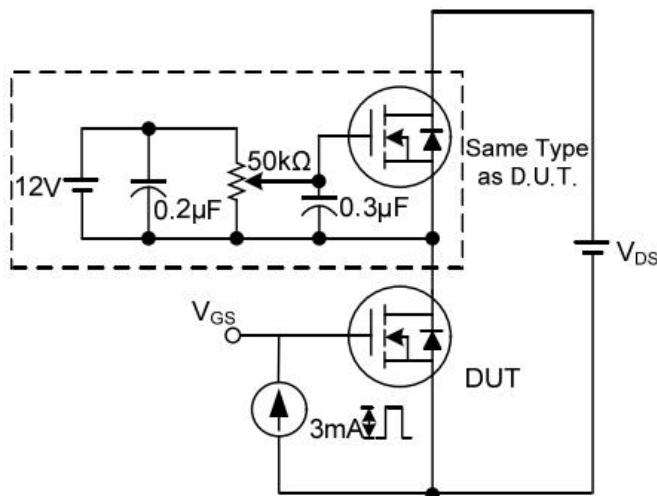


Peak Diode Recovery dv/dt Waveforms



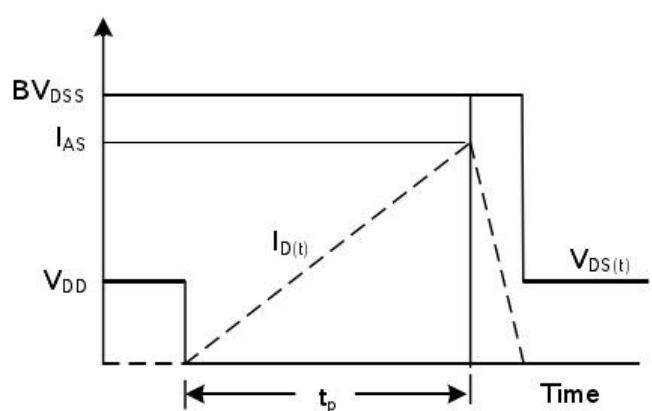
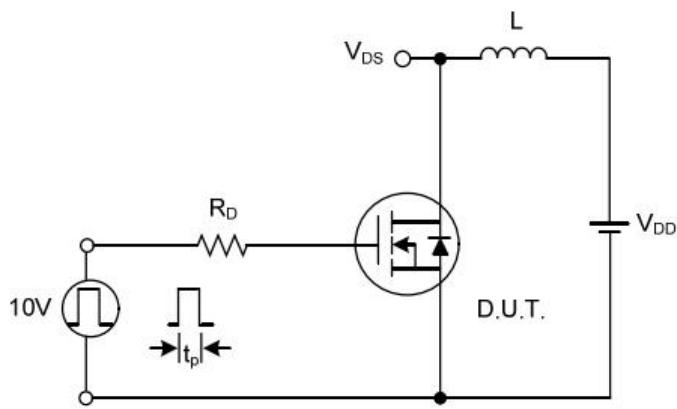
Switching Test Circuit

Switching Waveforms



Gate Charge Test Circuit

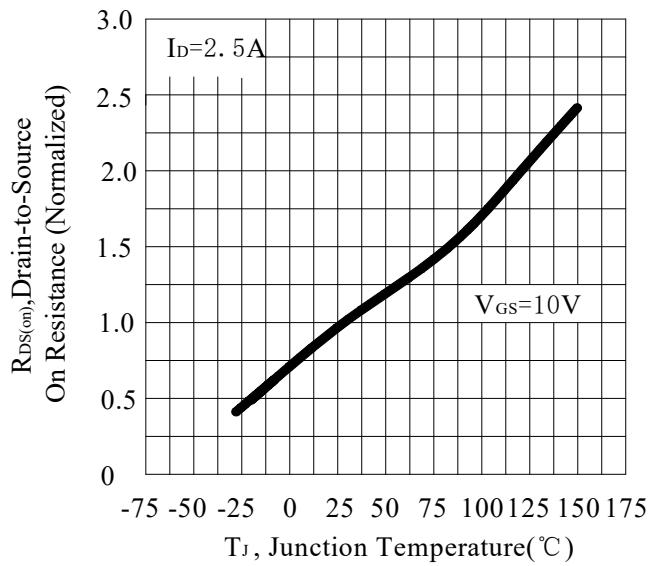
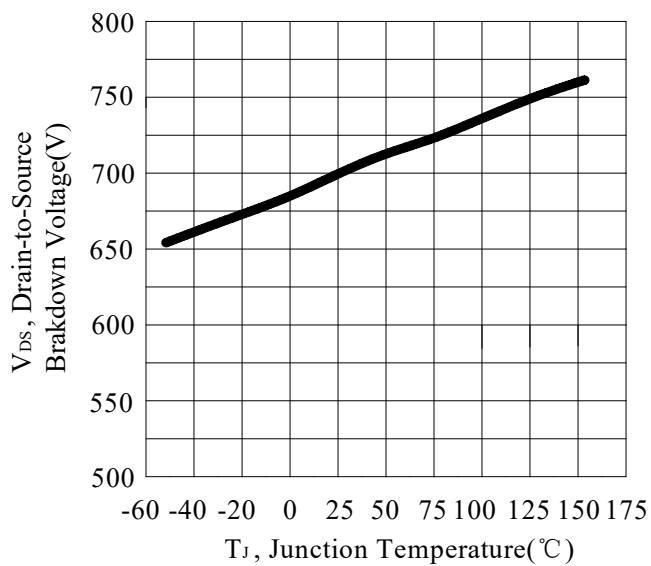
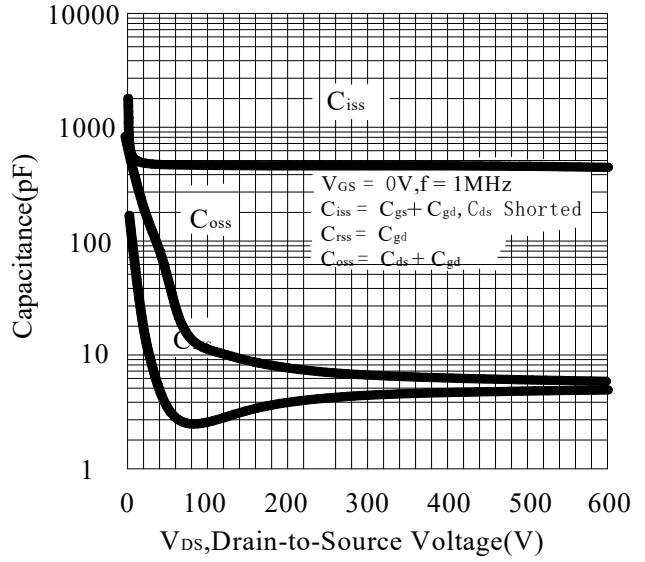
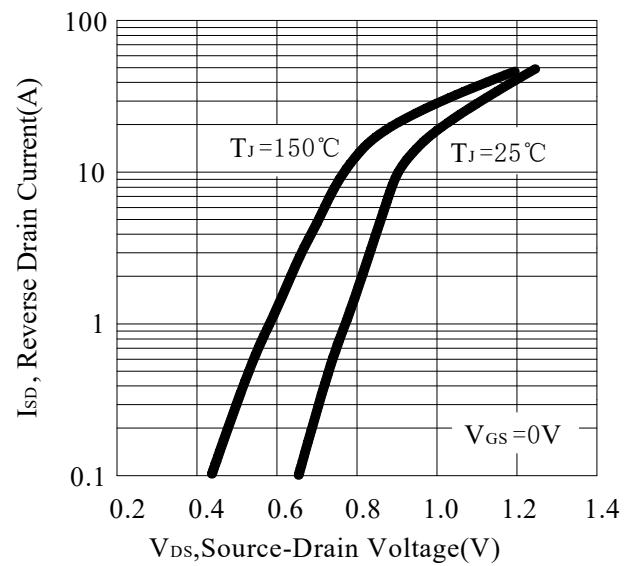
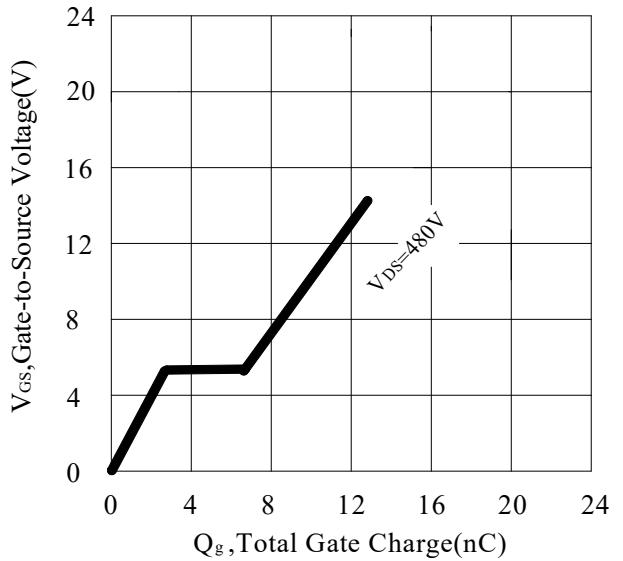
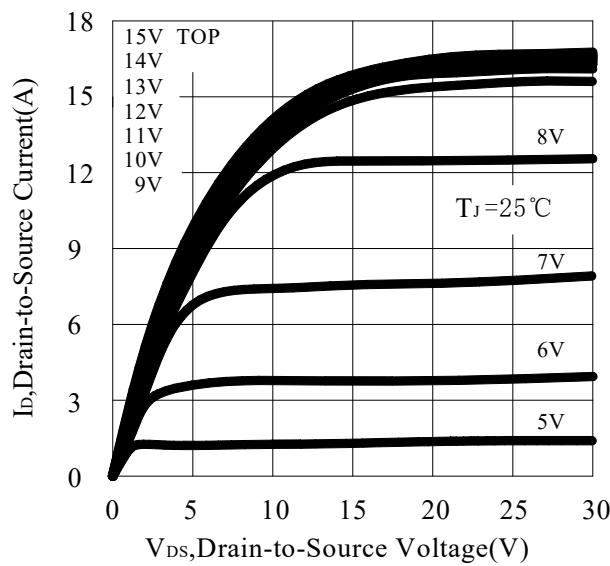
Gate Charge Waveform

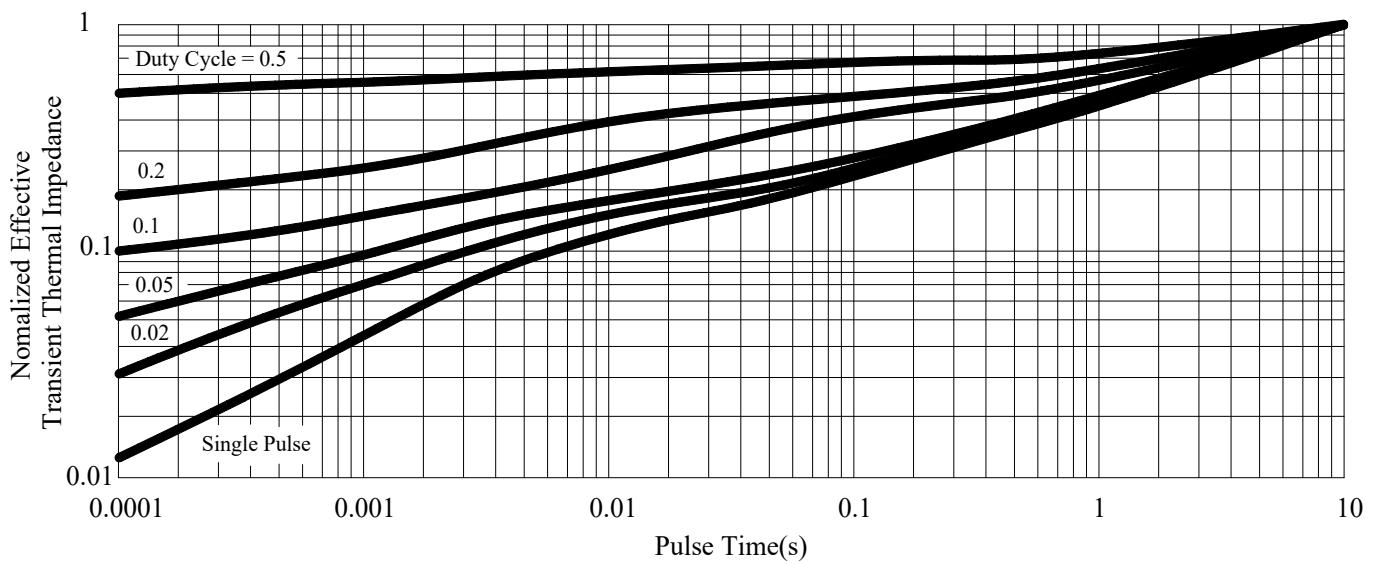
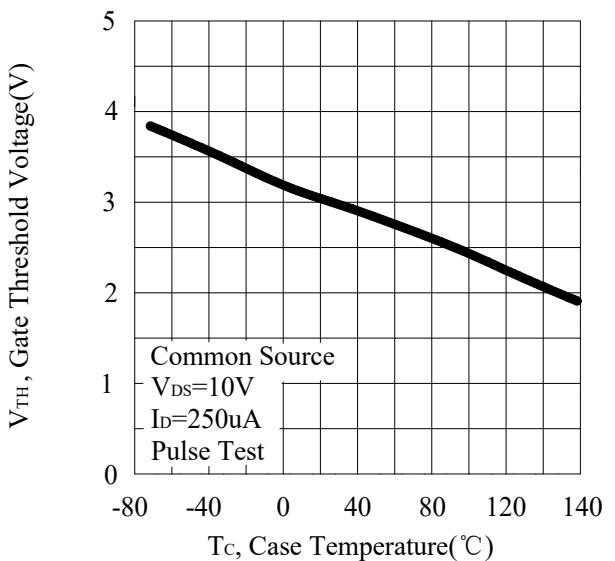
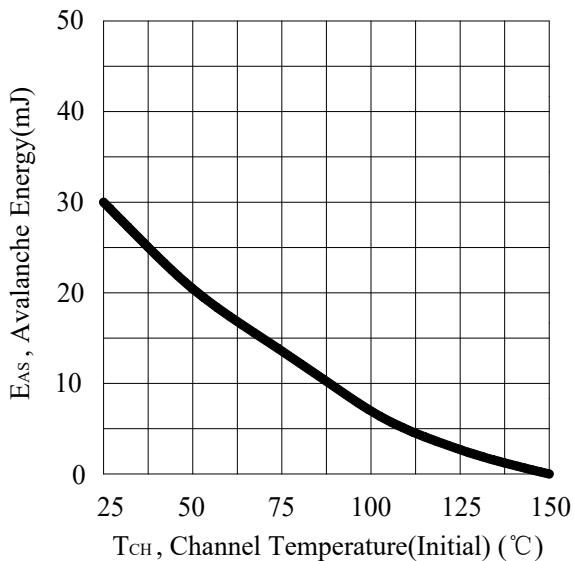
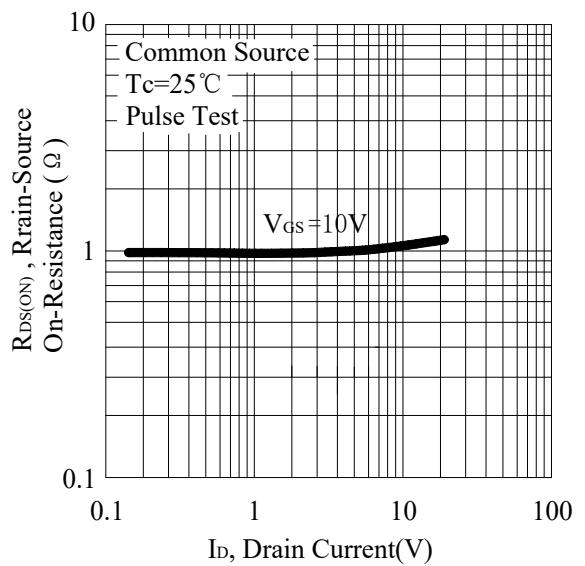
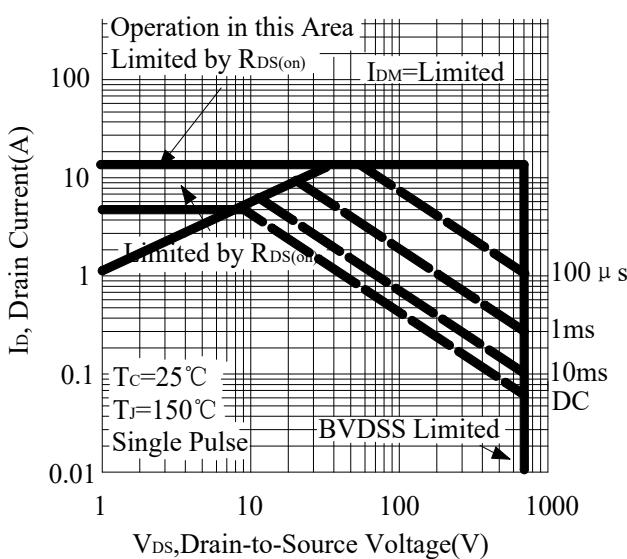


Unclamped Inductive Switching Test Circuit

Unclamped Inductive Switching Waveforms

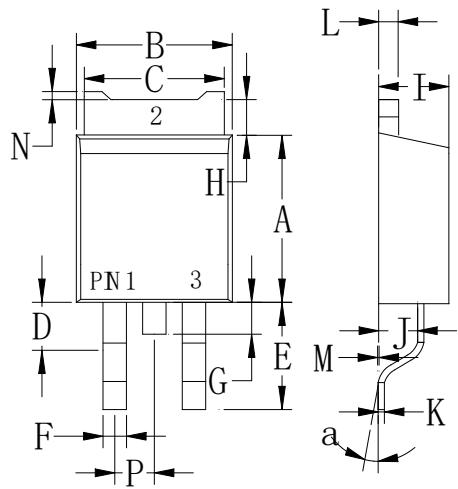
RATING AND CHARACTERISTIC CURVES





PACKAGE OUTLINE DIMENSIONS

TO-252



TO-252		
Dim	Min	Max
A	.230 (5.85)	.246 (6.25)
B	.250 (6.35)	.264 (6.75)
C	.207 (5.27)	.218 (5.54)
D	.037 (0.93)	.045 (1.14)
E	.106 (2.70)	.138 (3.50)
F	.028 (0.72)	.033 (0.84)
G	.024 (0.60)	.041 (1.05)
H	.028 (0.72)	.043 (1.10)
I	.085 (2.15)	.096 (2.45)
J	.037 (0.95)	.047 (1.20)
K	.018 (0.45)	.026 (0.65)
L	.018 (0.45)	.024 (0.60)
P	.081 (2.05)	.094 (2.40)
M	.000 (0.00)	.006 (0.15)
N	--	.008 (0.20)
a	0°	10°

Dimensions in inches and (millimeters)